AMENDMENTS TO THE CLAIMS

Listing of claims:

1-23 (Canceled)

24. (Currently amended): An apparatus, comprising:

a substrate;

a waveguide embedded within said substrate, wherein an optical signal may

propagate through said waveguide;

at least two or more light sources disposed on a first side of said substrate along a

length of said waveguide to emit light into said waveguide in at least partially a direction

substantially transverse to a direction of propagation of the optical signal, the light

emitted from said at least two or more light sources to pump the optical signal;

a reflector disposed on a second side of said substrate to reflect at least a portion

of light emitted from said at least two or more light sources into said waveguide, the

reflected light to pump the optical signal.

25. (Previously presented): An apparatus as claimed in claim 24, wherein said

waveguide is doped with erbium.

26. (Previously presented): An apparatus as claimed in claim 24, wherein the light source

is a vertical cavity emitting laser.

27. (Previously presented): An apparatus as claimed in claim 24, wherein light emitted

from said light source has a wavelength in the range of 980 nanometers to 1480

nanometers.

28. (Currently amended): An apparatus, comprising:

a semiconductor substrate;

a waveguide embedded within said semiconductor substrate through which an

optical signal may propagate; and

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at least two or more semiconductor light sources disposed on a first side of said

substrate along a length of said waveguide to emit light into said waveguide in a direction

at least partially substantially transverse to a direction of propagation of the optical

signal, the light emitted from said at least two or more semiconductor light sources to

pump the optical signal.

29. (Previously presented): An apparatus as claimed in claim 28, wherein said

waveguide is doped with erbium.

30. (Previously presented): An apparatus as claimed in claim 29, wherein the light source

is a vertical cavity emitting laser.

31. (Previously presented): An apparatus as claimed in claim 28, wherein light emitted

from said light source has a wavelength in the range of 980 nanometers to 1480

nanometers.

32. (Currently amended): An apparatus as claimed in claim 38 28, further comprising a

reflector disposed on a second side of said semiconductor substrate to reflect at least a

portion of the light emitted from said at least two or more semiconductor light sources

into said waveguide, wherein said reflector has a refractive index that is different than a

refractive index of said semiconductor substrate.

33. (Currently amended): An apparatus, comprising

a semiconductor substrate;

a waveguide embedded within said semiconductor substrate through which an

optical signal may propagate; and

at least two or more semiconductor light sources disposed on a first side of said

substrate along a length of the waveguide to emit light into said waveguide in a direction

substantially transverse to a direction of propagation of the optical signal, the light

emitted from said at least two or more semiconductor light sources to pump the optical

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signal, wherein at least two of said at least two or more semiconductor light sources are

disposed within a single light source substrate.

34. (Previously presented): An apparatus as claimed in claim 33, wherein said

waveguide is doped with erbium.

35. (Currently amended): An apparatus as claimed in claim 33, wherein at least a portion

of the light emitted from said light source is transverse perpendicular to a direction of

propagation of the optical signal through the waveguide.

36. (Previously presented): An apparatus as claimed in claim 33, wherein the light source

is a vertical cavity emitting laser.

37. (Previously Presented): An apparatus as claimed in claim 33, wherein light emitted

from said light source has a wavelength in the range of 980 nanometers to 1480

nanometers.

38. (Previously presented): An apparatus as claimed in claim 33, further comprising a

reflector disposed on a second side of said semiconductor substrate to reflect at least a

portion of the light emitted from said at least two or more semiconductor light sources

into the waveguide, wherein said reflector has a refractive index that is different than a

refractive index of said semiconductor substrate.

39. (Currently amended): An apparatus, comprising:

a semiconductor substrate;

a waveguide embedded within said semiconductor substrate through which an

optical signal may propagate, said waveguide being doped with erbium; and

at least two or more lasers disposed on a first side of said substrate along a length

of the waveguide to emit light into the waveguide in a direction substantially transverse

to a direction of propagation of the optical signal through said waveguide, the light

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emitted from said at least two or more lasers to pump the optical signal, wherein at least

two of said at least two or more lasers are disposed within a single laser substrate.

40. (Previously presented): An apparatus as claimed in claim 39, wherein at least one of

said two or more lasers is a vertical cavity emitting laser.

41. (Previously presented): An apparatus as claimed in claim 39, wherein light emitted

from said two or more lasers has a wavelength in the range of 980 nanometers to 1480

nanometers.

42. (Previously presented): An apparatus as claimed in claim 39, further comprising a

reflector disposed on a second side of said semiconductor substrate to reflect at least a

portion of the light emitted from said at least two or more lasers into the waveguide,

wherein said reflector has a refractive index that is different than a refractive index of

said semiconductor substrate.

43. (New): An apparatus as claimed in claim 24, wherein at least a portion of the light

emitted from said light source is perpendicular to a direction of propagation of the optical

signal through the waveguide.

44. (New): An apparatus as claimed in claim 28, wherein at least a portion of the light

emitted from said at least two or more semiconductor light source is perpendicular to a

direction of propagation of the optical signal through the waveguide.

45. (New): An apparatus as claimed in claim 39, wherein at least a portion of the light

emitted from said lasers source is perpendicular to a direction of propagation of the

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optical signal through the waveguide.

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